

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ)
25V	12A	60 @ V _{GS} = 10V
		85 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO252 and TO251 Package



ABSOLUTE MAXIMUM RATINGS (T_c=25. unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V _{spike} ^c	30	V
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	±16	V
Drain Current-Continuous @ T _c =25°C -Pulsed ^a	I _D	12	A
	I _{DM}	40	A
Drain-Source Diode Forward Current	I _S	5	A
Maximum Power Dissipation @ T _c =25°C	P _D	50	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C
THERMAL CHARACTERISTICS			
Thermal Resistance, Junction-to-Case	R _{θJC}	3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W